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8. (Amended) A method as claimed in claim 1 wherein the oxidation is carried out at a temperature in the range of from about 250° to about 500° C.

9. (Amended) A method for forming a capacitor comprising: providing a non-oxide electrode selected from the group consisting of TiN, TaN, WN, and W, oxidizing an upper surface of said non-oxide electrode using an O<sub>3</sub> gas plasma, depositing a high dielectric constant oxide dielectric material directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

Please cancel claim 14.

15. (Amended) A method as claimed in claim 9 wherein the oxidation is carried out at a temperature in the range of from about 250° to about 500° C.

16. (Amended) A method for forming a capacitor comprising: providing a non-oxide electrode selected from the group consisting of TiN, TaN, WN, and W, oxidizing an upper surface of said non-oxide electrode using an O<sub>3</sub> gas plasma, depositing a high dielectric constant oxide dielectric material selected from the group consisting of Al<sub>2</sub>O<sub>3</sub>, Ta<sub>2</sub>O<sub>5</sub> and Ba<sub>x</sub>Sr<sub>(1-x)</sub>TiO<sub>3</sub> directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

Please cancel claim 20.

21. (Amended) A method as claimed in claim 16 wherein the oxidation is carried out at a temperature in the range of from about 250° to about 500° C.

22. (Amended) A method for forming a capacitor comprising: providing a non-oxide electrode, in a deposition chamber oxidizing an upper surface of said non-oxide

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electrode, in the same deposition chamber depositing a high dielectric constant dielectric material directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

23. (Amended) A method for forming a capacitor comprising: providing a non-oxide electrode, oxidizing an upper surface of said non-oxide electrode at a temperature in the range of from about 250° to about 700° C in an atmosphere containing a gas selected from the group consisting of O<sub>2</sub>, O<sub>3</sub>, H<sub>2</sub>O, and N<sub>2</sub>O, depositing a high dielectric constant dielectric material directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

25. (Amended) A method for forming a capacitor comprising: providing a non-oxide electrode, oxidizing an upper surface of said non-oxide electrode in an atmosphere containing a gas plasma generated from a gas selected from the group consisting of O<sub>2</sub>, O<sub>3</sub>, H<sub>2</sub>O, and N<sub>2</sub>O, depositing a high dielectric constant dielectric material directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

38. (Amended) A method of forming a DRAM cell comprising providing a non-oxide electrode, oxidizing an upper surface of said non-oxide electrode, depositing a layer of a high dielectric constant oxide dielectric material directly onto the oxidized surface of said non-oxide electrode, depositing an upper layer electrode on said layer of said high dielectric constant oxide dielectric material, providing a field effect transistor having a pair of source/drain regions, electrically connecting one of said source/drain regions with said conductive oxide electrode and electrically connecting the other of said source/drain regions with a bit line.

41. (Amended) A method for forming a capacitor comprising: providing a non-oxide electrode selected from the group consisting of TiN, TaN, WN, and W, in a deposition chamber oxidizing an upper surface of said non-oxide electrode, in the same

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deposition chamber depositing a high dielectric constant oxide dielectric material directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

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42. (New) A method for forming a capacitor comprising: providing a non-oxide electrode; oxidizing an upper surface of said non-oxide electrode; depositing a high dielectric constant oxide dielectric material directly onto the oxidized surface of said non-oxide electrode; and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

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43. (New) A method for forming a capacitor comprising: providing a non-oxide electrode selected from the group consisting of TiN, TaN, WN, and W, oxidizing an upper surface of said non-oxide electrode, depositing a high dielectric constant oxide dielectric material directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

44. (New) A method for forming a capacitor comprising: providing a non-oxide electrode selected from the group consisting of TiN, TaN, WN, and W, oxidizing an upper surface of said non-oxide electrode, depositing a high dielectric constant oxide dielectric material selected from the group consisting of  $\text{Al}_2\text{O}_3$ ,  $\text{Ta}_2\text{O}_5$  and  $\text{Ba}_x\text{Sr}_{(1-x)}\text{TiO}_3$  directly onto the oxidized surface of said non-oxide electrode, and depositing an upper layer electrode on said high dielectric constant oxide dielectric material.

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#### Remarks

Claims 1-29 and 38-41 have been rejected. Claims 1, 8, 9, 15, 16, 21, 22, 23, 25, 38, and 41 have been amended. Claims 7, 14, and 20 have been canceled. New claims 42-44 have been added. Therefore, claims 1-6, 8-13, 15-19, 21-29, and 38-44 are pending in the present application.